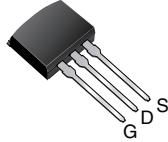
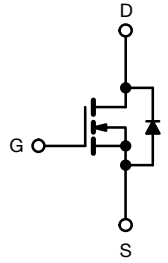
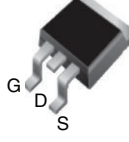


## Power MOSFET

 I<sup>2</sup>PAK (TO-262)

 D<sup>2</sup>PAK (TO-263)


N-Channel MOSFET

### FEATURES

- Surface-mount (IRFBC20S, SiHFBC20S)
- Low-profile through-hole (IRFBC20L, SiHFBC20L)
- Available in tape and reel (IRFBC20, SiHFBC20S)
- Dynamic dV/dt rating
- 150 °C operating temperature
- Fast switching
- Fully avalanche rated
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK is a surface-mount power package capable of the accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface-mount package. The D<sup>2</sup>PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface-mount application. The through-hole version (IRFBC20L, SiHFBC20L) is available for low-profile applications.

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	600	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	4.4
Q <sub>g</sub> max. (nC)	18	
Q <sub>gs</sub> (nC)	3.0	
Q <sub>gd</sub> (nC)	8.9	
Configuration	Single	

### ORDERING INFORMATION

Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	I <sup>2</sup> PAK (TO-262)
Lead (Pb)-free and halogen-free	SiHFBC20S-GE3	SiHFBC20STRL-GE3 <sup>a</sup>	SiHFBC20L-GE3
Lead (Pb)-free	IRFBC20SPbF	IRFBC20STRLPbF <sup>a</sup>	

### Note

a. See device orientation

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V <sub>DS</sub>	600	V
Gate-source voltage	V <sub>GS</sub>	± 20	V
Continuous drain current <sup>e</sup>	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	2.2
		T <sub>C</sub> = 100 °C	1.4
Pulsed drain current <sup>a, e</sup>	I <sub>DM</sub>	8.0	A
Linear derating factor		0.40	W/°C
Single pulse avalanche energy <sup>b, e</sup>	E <sub>AS</sub>	84	mJ
Avalanche current <sup>a</sup>	I <sub>AR</sub>	2.2	A
Repetitive avalanche energy <sup>a</sup>	E <sub>AR</sub>	5.0	mJ
Maximum power dissipation	P <sub>D</sub>	T <sub>A</sub> = 25 °C	3.1
		T <sub>C</sub> = 25 °C	50
Peak diode recovery dv/dt <sup>c, e</sup>	dv/dt	3.0	V/ns
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d</sup>	for 10 s	300	

### Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 31 mH, R<sub>G</sub> = 25 Ω, I<sub>AS</sub> = 2.2 A (see fig. 12)
- I<sub>SD</sub> ≤ 2.2 A, di/dt ≤ 40 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C
- 1.6 mm from case
- Uses IRFBC20, SiHFBC20 data and test conditions



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient (PCB mounted, steady-state) <sup>a</sup>	R <sub>thJA</sub>	-	40	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	2.5	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA	600	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA <sup>c</sup>	-	0.88	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	-	-	100	μA
		V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	500	
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V   I <sub>D</sub> = 1.3 A <sup>b</sup>	-	-	4.4	Ω
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.3 A <sup>c</sup>	1.4	-	-	S
<b>Dynamic</b>						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5 <sup>c</sup>	-	350	-	pF
Output capacitance	C <sub>oss</sub>		-	48	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	8.6	-	
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V   I <sub>D</sub> = 2.0 A, V <sub>DS</sub> = 360 V, see fig. 6 and 13 <sup>b, c</sup>	-	-	18	nC
Gate-source charge	Q <sub>gs</sub>		-	-	3.0	
Gate-drain charge	Q <sub>gd</sub>		-	-	8.9	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 2.0 A, R <sub>g</sub> = 18 Ω, R <sub>D</sub> = 150 Ω, see fig. 10 <sup>b, c</sup>	-	10	-	ns
Rise time	t <sub>r</sub>		-	23	-	
Turn-off delay time	t <sub>d(off)</sub>		-	30	-	
Fall time	t <sub>f</sub>		-	25	-	
Gate input resistance	R <sub>g</sub>	f = 1 MHz, open drain	1.2	-	7.4	Ω
Internal source inductance	L <sub>S</sub>	Between lead, and center of die contact	-	7.5	-	nH
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	2.2	A
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>		-	-	8.0	
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 2.2 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.6	V
Body diode reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 2.0 A, dI/dt = 100 A/μs <sup>b, c</sup>	-	290	580	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	0.67	1.3	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %
- c. Uses IRFBC20, SiHFBC20 data and test conditions



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

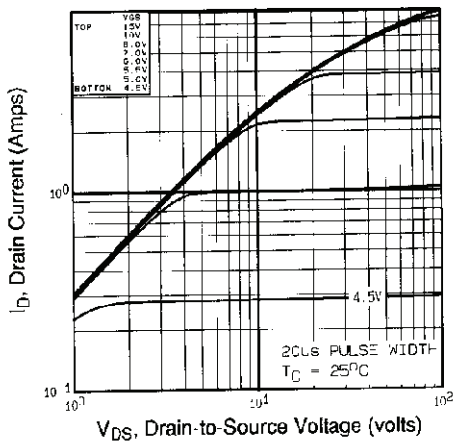


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

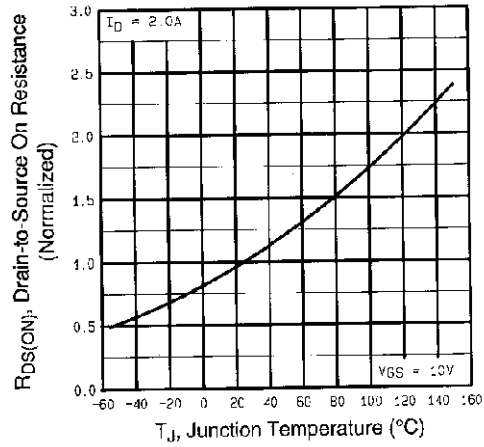


Fig. 4 - Normalized On-Resistance vs. Temperature

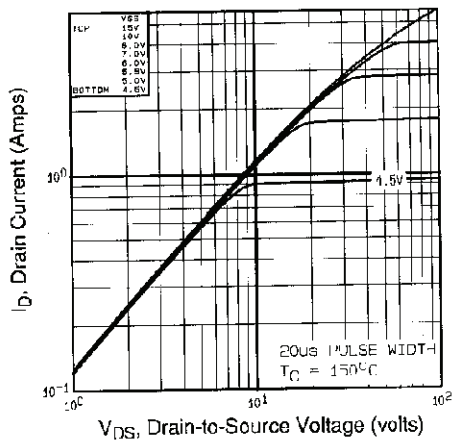


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

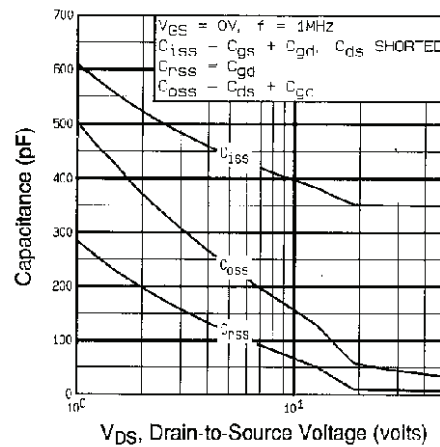


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

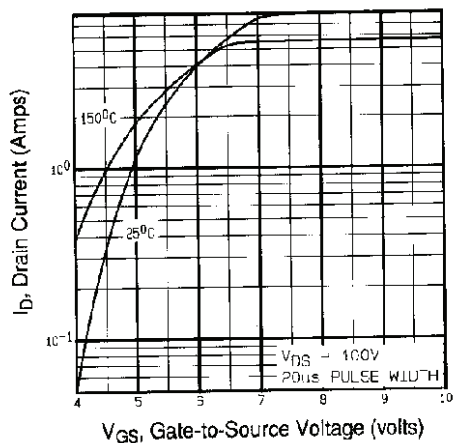


Fig. 3 - Typical Transfer Characteristics

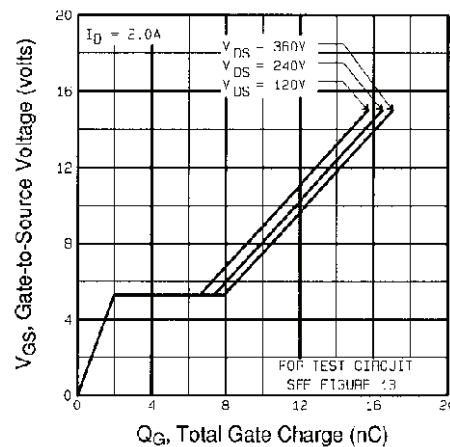


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

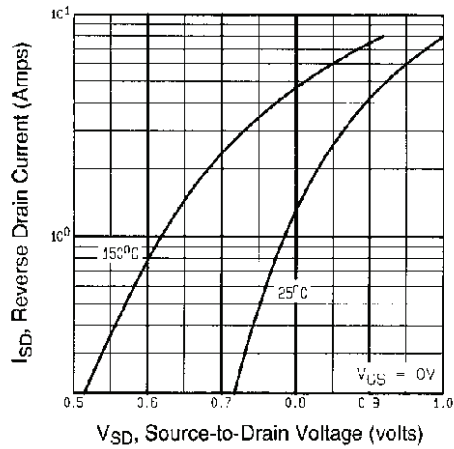


Fig. 7 - Typical Source-Drain Diode Forward Voltage

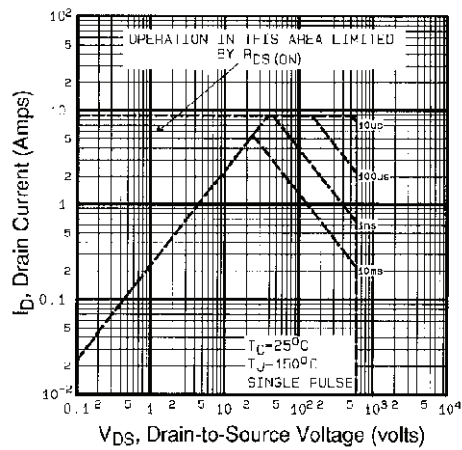


Fig. 8 - Maximum Safe Operating Area

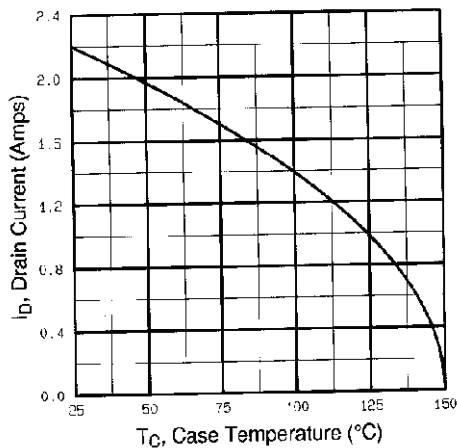


Fig. 9 - Maximum Drain Current vs. Case Temperature

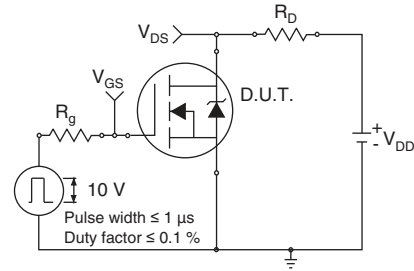


Fig. 10a - Switching Time Test Circuit

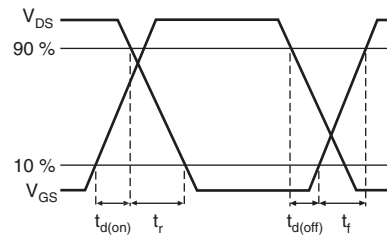
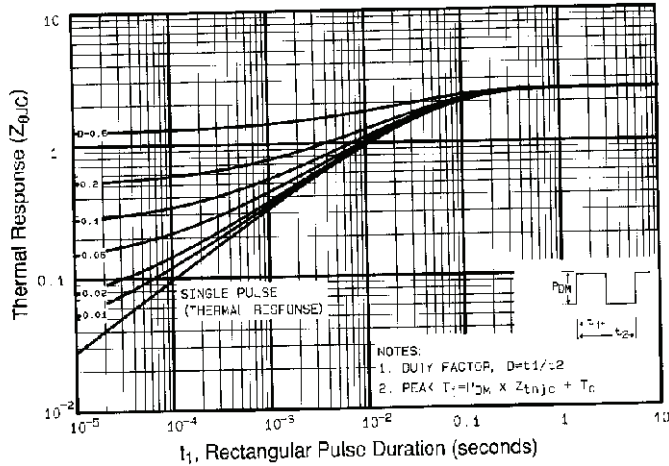
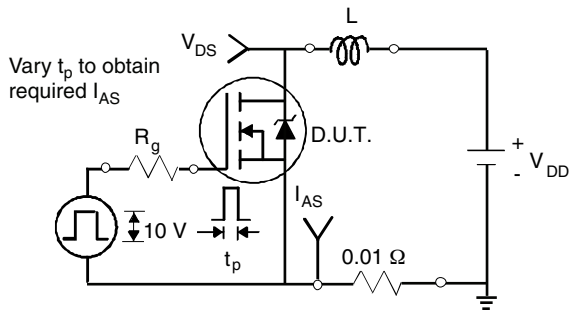


Fig. 10b - Switching Time Waveforms

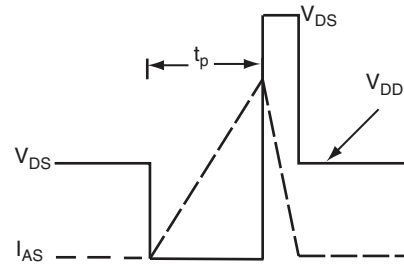
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



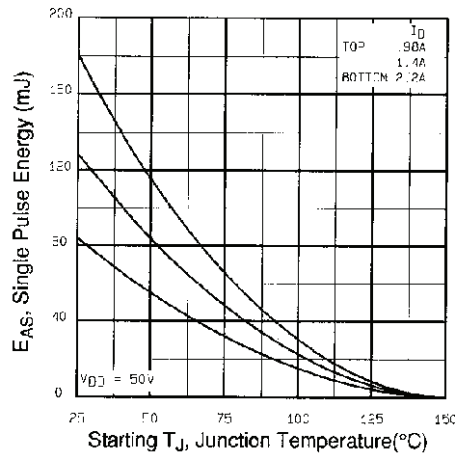
**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



**Fig. 12a - Unclamped Inductive Test Circuit**



**Fig. 12b - Unclamped Inductive Waveforms**



**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**

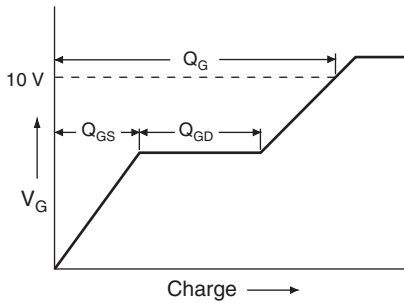


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

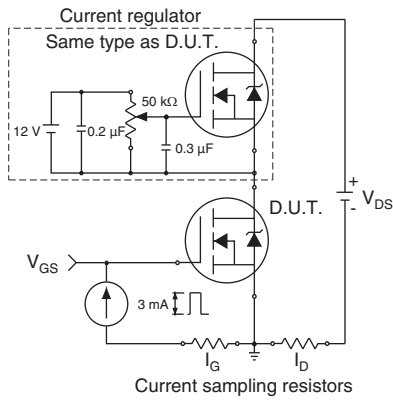
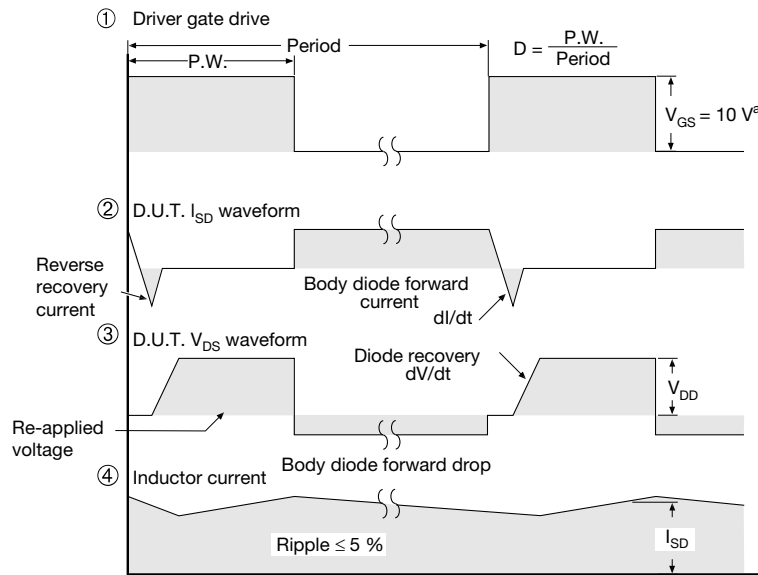
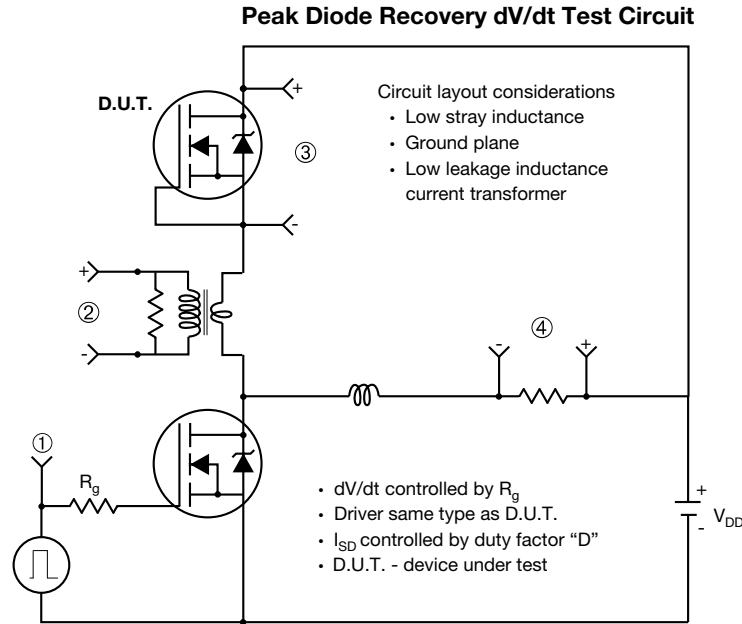


Fig. 13b - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

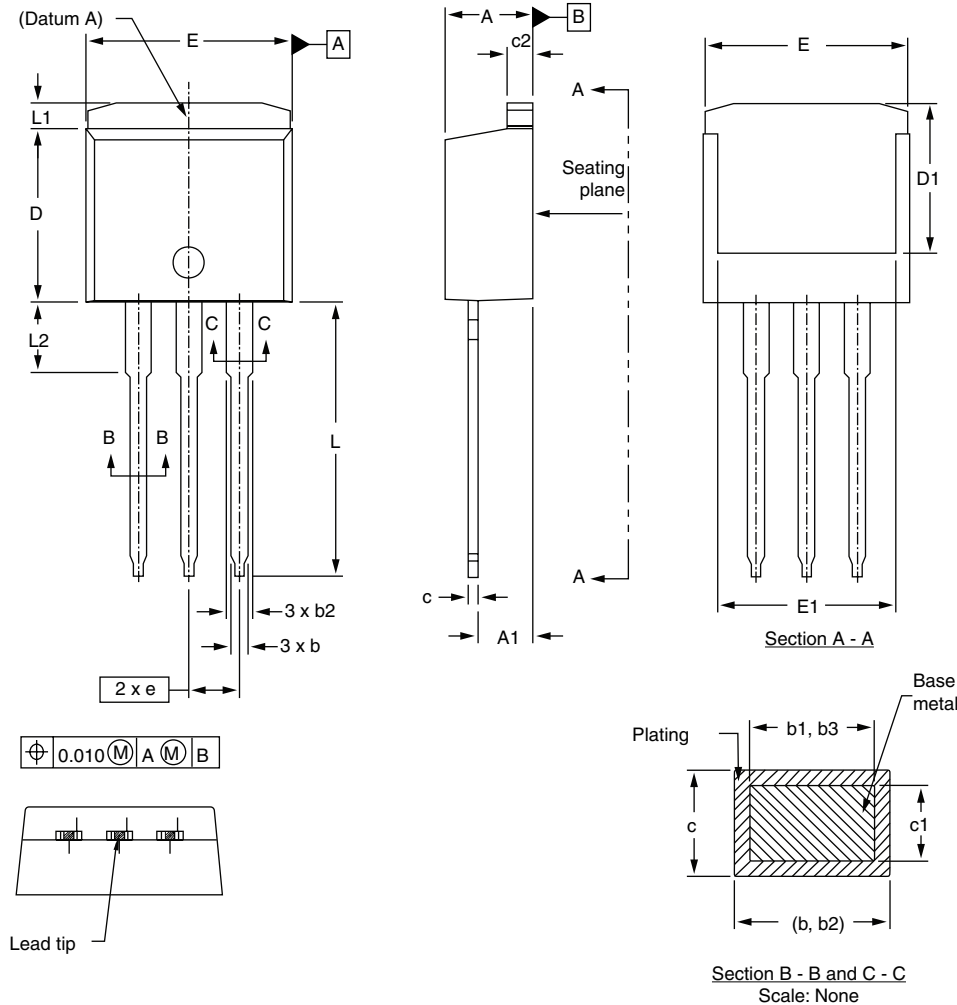
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

## I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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